



AP
2800

PATENT
Docket No.: ACT-307DVA

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2814 Examiner: Mai, Anh D.
Serial No. 10/036,303 Filed: December 28, 2001
In re Application of: Hawley, et al.
For: METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED TOTAL
RADIATION-INDUCED LEAKAGE CURRENT

Certificate of Mailing
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail, in an envelope addressed to Commissioner for Patents, Box AF, Washington, D.C. 20231, on 3/26/03, Signed Martha N. Griffin
Martha N. Griffin

TRANSMITTAL LETTER

Box AF
Commissioner for Patents
Washington, D.C. 20231

Dear Sir:


Responsive to the Final Office Action mailed December 26, 2002, please find enclosed herewith:

1. Response to Office Action (4 pages); and
2. Declaration Under 37 CFR 1.132 (3 pages);

In the event any variance exists between the amount enclosed and the patent office charges for filing the above-noted documents, including any fees required under 37 CFR 1.136 for any necessary Extension of Time to make the filing of the attached documents timely, the Assistant Commissioner is hereby authorized to charge or credit the difference to our Deposit Account No. 50-0612. An additional copy of this page is enclosed.

Respectfully submitted,
Sierra Patent Group, Ltd.

Dated: March 26, 2003


Andrew D. Gathy
Reg. No. 46,441, for:
Kristin C. Castle
Reg. No. 47,208

Sierra Patent Group, Ltd.
P.O. Box 6149
Stateline, NV 89449
(775) 586-9500

RECEIVED
APR - 3 2003
TECHNOLOGY CENTER 2800